

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

[[an]] a MOS capacitor that comprises,

a first-conductivity-type diffusion layer formed in a surface of a substrate,

a gate oxide film formed on said first-conductivity-type diffusion layer, and

a first polysilicon layer formed on said gate oxide film and doped with a dopant of the

~~first conductivity-type~~ first-conductivity-type or a ~~second conductivity-type~~ second-conductivity-type; and

a Poly-Poly capacitor that comprises,

said first polysilicon layer,

a first dielectric layer formed on said first polysilicon layer to cover each of first and second side faces of said first polysilicon layer, and

a second polysilicon layer formed on said first dielectric layer and doped with a dopant of the ~~first conductivity-type~~ first-conductivity-type or the second conductivity type,

said Poly-Poly capacitor being stacked on said MOS capacitor, and

said first-conductivity-type diffusion layer and said second polysilicon layer being electrically connected to a same first metal interconnection.

Claim 2 (Currently Amended): The semiconductor device according to claim 1, further comprising:

a PN-junction capacitor comprising said first-conductivity-type diffusion layer and a second-conductivity-type diffusion layer formed under said first-conductivity-type diffusion layer,

adjacent to the element region where said MOS capacitor resides, with said trench isolation oxide film interposed therebetween.

Claim 5 (Currently Amended): A semiconductor device comprising:

a substrate;

an interlayer insulating layer formed on said substrate; and

a first Poly-Poly capacitor formed within said interlayer insulating layer and comprising: that comprises,

a spiral-shaped first polysilicon electrode,

a spiral-shaped second polysilicon electrode formed parallel to the shape of ~~to the shape of~~
with said first polysilicon electrode, and

a ~~third~~ first dielectric layer interposed only between said first polysilicon electrode and said second polysilicon electrode, wherein
said first dielectric layer has a dielectric constant higher than a dielectric constant of
said interlayer insulating layer.

Claim 6 (Canceled).

Claim 7 (Currently Amended): The semiconductor device according to claim 5, further comprising a second Poly-Poly capacitor that comprises:

a spiral-shaped third polysilicon electrode;

a spiral-shaped fourth polysilicon electrode formed parallel to the shape of said third polysilicon electrode; and


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Expires: December 26, 2004



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